

2SK1313(L)(S), 2SK1314(L)(S)

Silicon N-Channel MOS FET

HITACHI

Application

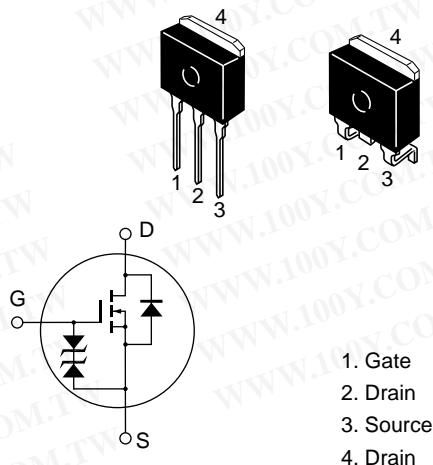
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline

LDPAK



2SK1313(L)(S), 2SK1314(L)(S)

Absolute Maximum Ratings (Ta = 25°C)

勝特力材料 886-3-5753170

勝特力电子(上海) 86-21-54151736

勝特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1313	V_{DSS}	450	V
	2SK1314		500	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I_D	5	A
Drain peak current		$I_{D(pulse)}^{*1}$	20	A
Body to drain diode reverse drain current		I_{DR}	5	A
Channel dissipation		P_{ch}^{*2}	50	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

2. Value at $T_c = 25^\circ C$

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK1313 $V_{(BR)DSS}$	450	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
	2SK1314	500	—	—	—	—
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 30	—	—	V	$I_G = \pm 100 \mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 25 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	2SK1313 I_{DSS}	—	—	250	μA	$V_{DS} = 360 \text{ V}$, $V_{GS} = 0$
	2SK1314	—	—	—	—	$V_{DS} = 400 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static Drain to source on state resistance	2SK1313 $R_{DS(on)}$	—	1.0	1.4	Ω	$I_D = 2.5 \text{ A}$, $V_{GS} = 10 \text{ V}^{*1}$
	2SK1314	—	1.2	1.5	—	—
Forward transfer admittance	$ y_{fs} $	2.5	4.0	—	S	$I_D = 2.5 \text{ A}$, $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	640	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$,
Output capacitance	C_{oss}	—	160	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	C_{rss}	—	20	—	pF	—
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$I_D = 2.5 \text{ A}$, $V_{GS} = 10 \text{ V}$,
Rise time	t_r	—	25	—	ns	$R_L = 12 \Omega$
Turn-off delay time	$t_{d(off)}$	—	50	—	ns	—
Fall time	t_f	—	30	—	ns	—
Body to drain diode forward voltage	V_{DF}	—	0.95	—	V	$I_F = 5 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	300	—	ns	$I_F = 5 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 100 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

See characteristic curves of 2SK1155, 2SK1156.

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

2SK1313(L)(S), 2SK1314(L)(S)

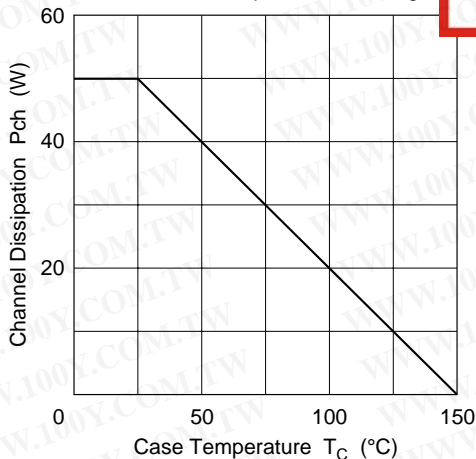
勝特力材料 886-3-5753170

勝特力电子(上海) 86-21-54151736

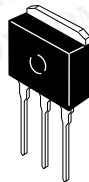
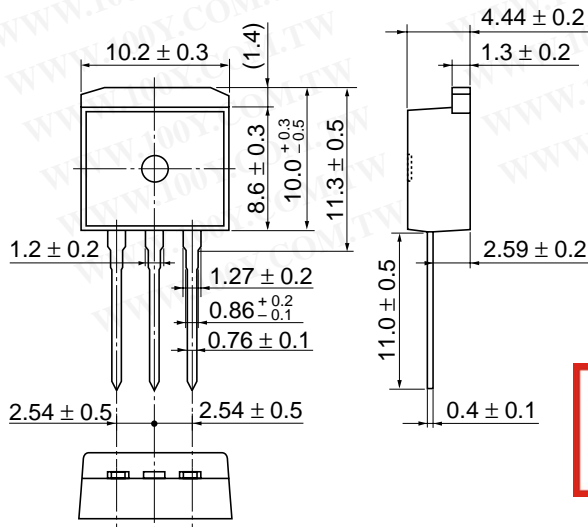
勝特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)

Power vs. Temperature Derating



Unit: mm



勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Hitachi Code	LPAK (L)
JEDEC	—
EIAJ	—
Weight (reference value)	1.4 g

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Cautions

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
5. This product is not designed to be radiation resistant.
6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

HITACHI